

ZDS020N60

Nch 600V 0.63A Power MOSFET

V _{DSS}	600V
R _{DS(on)} (Max.)	5.0Ω
I _D	0.63A
P_D	2.0W

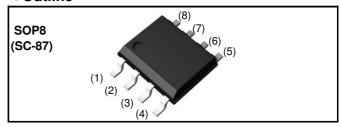
Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (V_{GSS}) guaranteed to be $\pm 30V$.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating; RoHS compliant

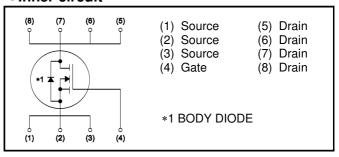
Application

Switching Power Supply

Outline



●Inner circuit



Packaging specifications

	Packaging	Taping
	Reel size (mm)	330
Tuno	Tape width (mm)	12
Туре	Basic ordering unit (pcs)	2,500
	Taping code	ТВ
	Marking	ZDS020N60

• Absolute maximum ratings($T_a = 25 \,^{\circ}\text{C}$)

Paramete	Symbol	Value	Unit	
Drain - Source voltage	V_{DSS}	600	V	
Continuous drain current	T _c = 25 °C	I _D *1	±0.63	А
Pulsed drain current		I _{D,pulse} *2	±2.5	А
Gate - Source voltage		V _{GSS}	±30	V
Power dissipation $(T_c = 25^{\circ}C)$		P _D	2.0	W
Junction temperature		T _j	150	℃
Range of storage temperature		T _{stg}	-55 to +150	∞

●Thermal resistance

Parameter	Symbol	Values			Unit
Farameter	Зушьог	Min.	Тур.	Max.	Offic
Thermal resistance, junction - ambient	R_{thJA}	ı	-	62.5	°C/W

ullet Electrical characteristics (T_a = 25 °C)

Parameter	Symbol	Conditions		Unit		
Farameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$, $I_D = 1mA$	600	1	-	V
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 600V, V_{GS} = 0V$	-		100	μΑ
Gate - Source leakage current	I _{GSS}	$V_{GS} = \pm 30V, \ V_{DS} = 0V$	ı	ı	±100	nA
Gate threshold voltage	V _{GS (th)}	$V_{DS} = 10V$, $I_D = 1mA$	2.0	ı	4.0	V
Static drain - source on - state resistance	R _{DS(on)} *3	$V_{GS} = 10V, I_D = 0.5A$	-	4.4	5.0	Ω

ullet Electrical characteristics($T_a = 25\,^{\circ}C$)

Parameter	Symbol	Conditions		Unit		
raiametei	Symbol	Conditions	Min.	Тур.	Max.	Ullit
Transconductance	g _{fs} *3	$V_{DS} = 10V, I_D = 0.5A$	0.05	0.5	-	S
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	310	-	
Output capacitance	C _{oss}	V _{DS} = 10V	-	145	-	pF
Reverse transfer capacitance	C_{rss}	f = 1MHz	ı	40	-	
Turn - on delay time	$t_{d(on)}^{*3}$	$V_{DD} \simeq 200V, V_{GS} = 10V$	ı	25	-	
Rise time	t _r *3	I _D = 600mA	ı	20	-	nc
Turn - off delay time	t _{d(off)} *3	$R_L = 333\Omega$	-	65	-	ns
Fall time	t _f *3	$R_G = 50\Omega$	-	65	-	

ullet Gate Charge characteristics(T_a = 25 °C)

Parameter	Cymbol	Conditions		Unit		
raiametei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	Q_g^{*3}	$V_{DD} \simeq 450V$	-	12	20	
Gate - Source charge	Q _{gs} *3	$I_D = 600 \text{mA}$	-	3	-	nC
Gate - Drain charge	Q _{gd} *3	V _{GS} = 10V	-	5	1	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} \simeq 450V$, $I_D = 600mA$	ı	5	-	V

^{*1} Limited only by maximum temperature allowed.

^{*2} Pw \leq 10 μ s, Duty cycle \leq 1%

^{*3} Pulsed

ullet Body diode electrical characteristics (Source-Drain)(T_a = 25 °C)

Parameter	Symbol	Conditions	Values			Unit
r arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l _S *1	T _c = 25℃	-	1	0.63	А
Inverse diode direct current, pulsed	I _{SM} *2	11c - 25 0	-	-	2.5	Α
Forward voltage	V _{SD} *3	$V_{GS} = 0V, I_{S} = 1A$	-	-	1.5	V

• Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

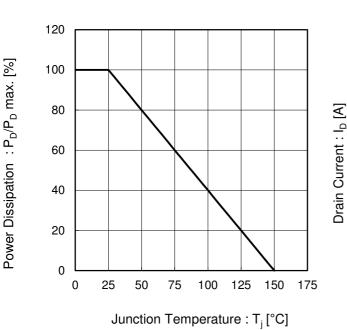
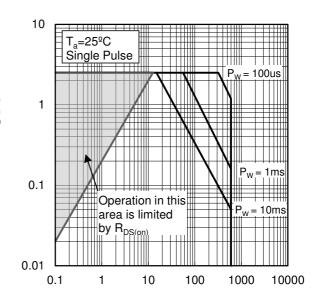
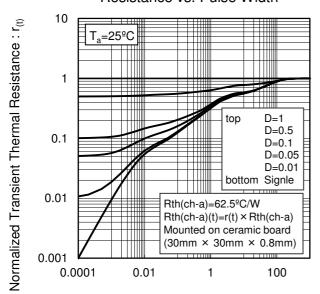


Fig.2 Maximum Safe Operating Area



Drain - Source Voltage : $V_{DS}[V]$

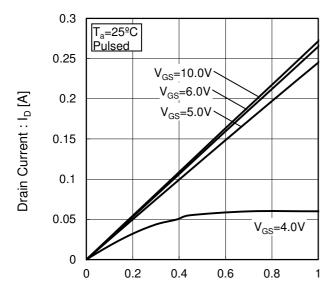
Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



Pulse Width: Pw[s]

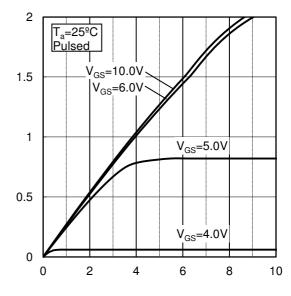
• Electrical characteristic curves

Fig.4 Typical Output Characteristics(I)



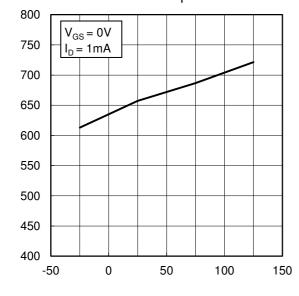
Drain - Source Voltage : V_{DS} [V]

Fig.5 Typical Output Characteristics(II)



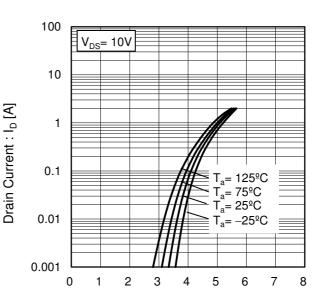
Drain - Source Voltage : V_{DS} [V]

Fig.6 Breakdown Voltage vs. Channel Temperature



Junction Temperature : T_i [°C]

Fig.7 Typical Transfer Characteristics



Gate - Source Voltage : V_{GS} [V]

Drain - Source Breakdown Voltage : $V_{(BR)DSS}\left[V\right]$

Drain Current : I_D [A]

•Electrical characteristic curves

Fig.8 Gate Threshold Voltage vs. Channel Temperature 5.0 $V_{DS} = 10V$ $I_D = 1mA$ Gate Threshold Voltage: V_{GS(th)} [V] 4.0 3.0 2.0 1.0 0.0 -50 -25 0 25 50 75 100 125 150 Junction Temperature : T_i [°C]

100 V_{DS}= 10V 10 1 T_a= -25°C T_a=25°C

Fig.9 Transconductance vs. Drain Current

Drain Current : I_D [A]

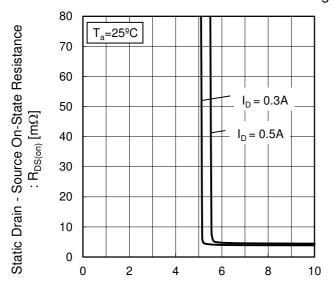
10

100

T_a=75°C T_a=125°C

1

Fig.10 Static Drain - Source On - State Resistance vs. Gate Source Voltage



Gate - Source Voltage : $V_{GS}[V]$

Transconductance: g_{fs} [S]

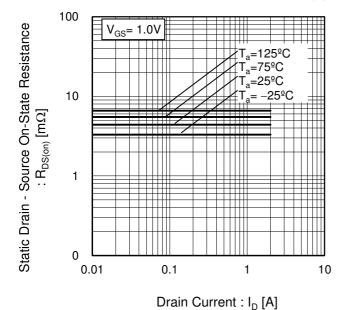
0.01

0.01

0.1

• Electrical characteristic curves

Fig.11 Static Drain - Source On - State Resistance vs. Drain Current(II)



10 $V_{GS} = 10V$ $I_D = 2A$ 9 8

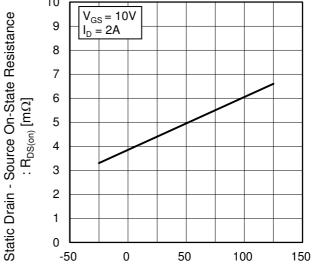


Fig.12 Static Drain - Source On - State Resistance vs. Junction Temperature

Junction Temperature : T_i [°C]

•Electrical characteristic curves

Fig.13 Typical Capacitance vs. Drain - Source Voltage

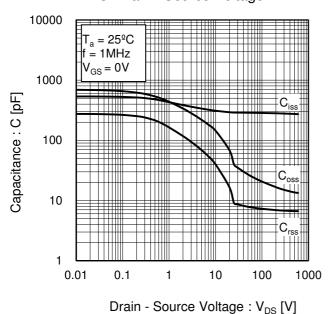
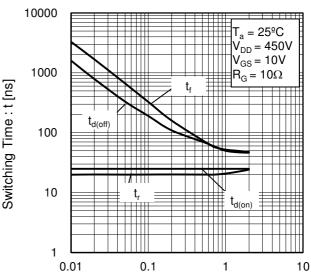
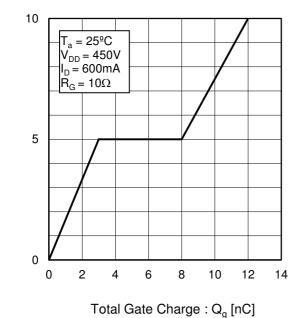


Fig.14 Switching Characteristics



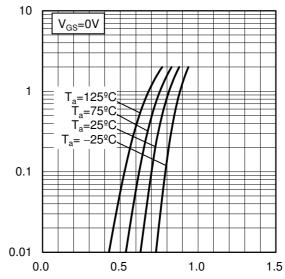
Drain Current : I_D [A]

Fig.15 Dynamic Input Characteristics



Inverse Diode Forward Current : $I_{\rm S}$ [A]

Fig.16 Inverse Diode Forward Current vs. Source - Drain Voltage



Source - Drain Voltage : V_{SD} [V]

Gate - Source Voltage : V_{GS} [V]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

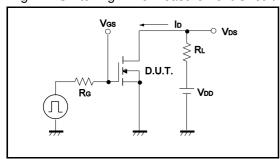


Fig.2-1 Gate Charge Measurement Circuit

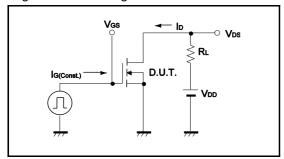


Fig.1-2 Switching Waveforms

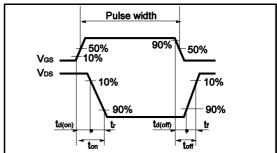
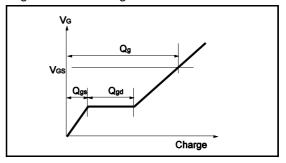
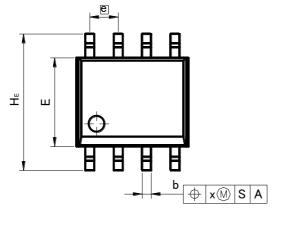


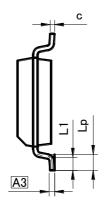
Fig.2-2 Gate Charge Waveform

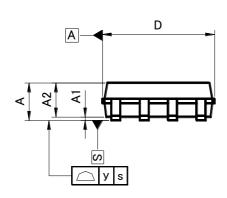


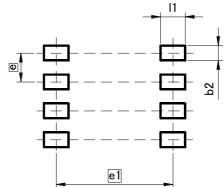
●Dimensions (Unit:mm)











Patterm of terminal position areas

DIM	MILIM	MILIMETERS		HES
DIM	MIN	MAX	MIN	MAX
Α	_	1.75	_	0.069
A1	0.	15	0.0	006
A2	1.40	1.60	0.055	0.063
A3	0.3	25	0.	01
b	0.30	0.50	0.012	0.02
С	0.10	0.30	0.004	0.012
D	4.80	5.20	0.189	0.205
Е	3.75	4.05	0.148	0.159
е	1.27		0.	05
HE	5.70	6.30	0.224	0.248
L1	0.50	0.70	0.02	0.028
Lp	0.65	0.85	0.026	0.033
х	0.	0.15		06
У	0.	0.10		004

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
b2	_	0.65	- 0.026		
e1	5.	15	0.2	03	
l1	_	1.15	_	0.045	

Dimension in mm/inches

Notes

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